

WSR90N07

N-Ch MOSFET

General Description

The WSR90N07 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

Product Summery

BV _{DSS}		I _D
72V	6.8mΩ	84A

Applications

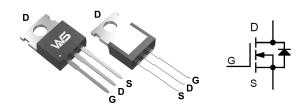
Switch.

Load.

TO-220FB-3L Pin Configuration



- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available



Absolute	Maximum	Ratings

Symble	Parameter	Rating	Units
Vds	Drain-to-Source voltage	72	V
Vgs	Gate-to-Source voltage	±20	V
lo	Continuous drain current,VGS@10V (Tc=25°C)	84	A
U	Continuous drain current,VGS@10V(Tc=100°C)	76	A
Ідм	Pulsed drain current ①	310	А
Dr	Power dissipation (Tc=25°C)	181	W
PD	Linear derating factor (Tc=25℃)	1.5	₩/° C
Eas	Single pulse avalanche energy ②	400	mJ
Тј Тѕтс	Operating Junction and Storage Temperature Range	–55 to +175	°C
dv/dt	Peak diode recovery voltage	31	v/ns
Ear	Repetitive avalanche energy	TBD	

Thermal Resistance

Symbol	Parameter	Min.	Тур.	Max.	Units
Rejc	Junction-to-case	-	0.83	-	°C/W
Reja	Junction-to-ambient	-	-	62	°C/W



N-Ch MOSFET

Electrical Characteristics @TJ=25°C (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BVDSS	Drain-to-Source breakdown voltage	V _{GS} =0V,I _D =250µA	72	-	-	V
IDSS	Drain-to-Source leakage current	VDS=68V,VGS=0V	-	-	2	
		V⊳s=68V, V₀s=0V,TJ=150°C	-	-	10	μA
lgss	Gate-to-Source forward leakage	V _{GS} =20V	-	-	100	nA
IGSS	Gate-to-Source reverse leakage	V _{GS} =-20V	-	-	-100	
$V_{GS(th)}$	Gate threshold voltage	Vbs=Vgs,Ib=250µA	2.0	-	4.0	V
RDS(on)	Static Drain-to-Source on-resistance	Vgs=10V,Id=30A	-	7.2	8	mΩ
Qg	Total gate charge		-	90	-	nC
Qgs	Gate-to-Source charge	ID=30A VDD=30V VGS=10V	-	18	-	
Qgd	Gate-to-Drain("Miller") charge		_	28	-	
t d(on)	Turn-on delay time		-	18.2	-	
tr	Rise time	V _{DD} =30V I _D =2A ,R∟=15Ω R _G =2.5Ω V _{GS} =10V	-	15.6	-	nS
td(off)	Turn-Off delay time		_	70.5	-	113
tr	Fall time		-	13.8	-	,
Ciss	Input capacitance	V _{GS} =0V V _{DS} =25V f=1.0MHZ	-	3150	-	
Coss	Output capacitance		-	300	-	pF
Crss	Reverse transfer capacitance		-	240	-	

Source-Drain Ratings and Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
ls	Continuous Source Current (Body Diode)		-	-	84	A
Ism	Pulsed Source Current (Body Diode) ①	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	310	A
Vsd	Diode Forward Voltage	TJ =25 ℃,Is =68A,V Gs =0V ③	-	-	1.3	V
trr	Reverse Recovery Time	Tյ=25℃,I⊧=68A,di/dt=100A/µs ③	-	57	-	nS
Qrr	Reverse Recovery Charge		-	107	-	nC
ton	Forward Turn-on Time	Intrinsic turn-on time is negligible (turn-on is dominated by Ls + LD)				

Notes:

① Repetitive rating; pulse width limited by max junction temperature.

2 Test condition: L =0.3mH, ID = 37A, VDD = 30V

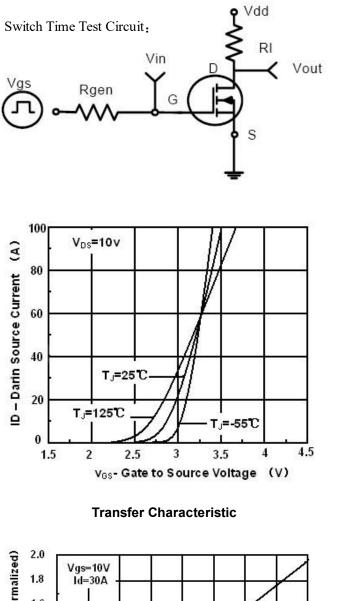
③ Pulse width≤300µS, duty cycle≤1.5% ; RG = 25Ω Starting TJ = 25°C



WSR90N07

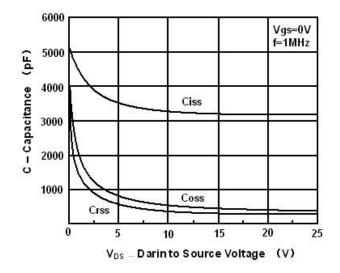
N-Ch MOSFET

Typical Operating Characteristics

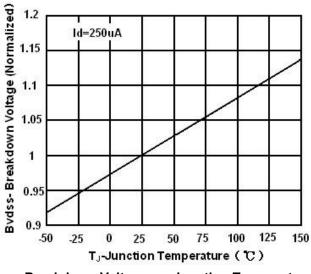


RDS (01) -On Resistance (Normalized) 1.6 1.4 1.2 1.0 0.8 0.6 0.4 125 150 -25 25 50 75 100 -50 0 T_J-Junction Temperature ($^{\circ}C$) **On Resistance vs. Junction Temperature**

Switch Waveforms: Vds $\overline{90\%}$ $\overline{10\%}$ $\overline{10\%}$ $\overline{10\%}$ $\overline{10\%}$







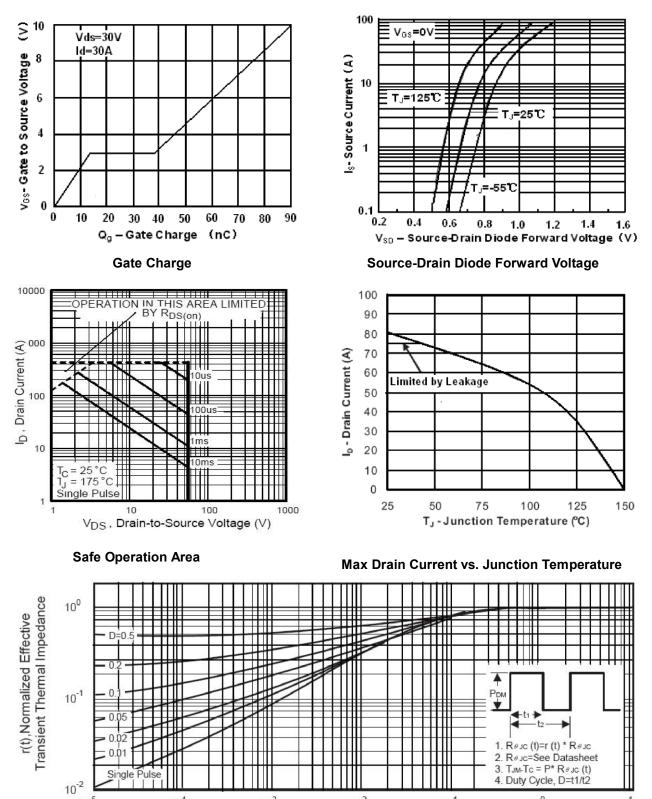
Breakdown Voltage vs. Junction Temperature



WSR90N07

N-Ch MOSFET

Typical Operating Characteristics (Cont.)



Square Wave Pulse Duration (sec)

10-3

Transient Thermal Impedance Curve

10⁻²

10⁻¹

10⁻⁵

10⁻⁴

10¹

10⁰



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